Adele Sassella

List of Publications by Year
in descending order

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183 papers	3,239 citations	159585 30 h-index	206112 48 g-index
185 all docs	185 docs citations	185 times ranked	2708 citing authors

#	Article	IF	Citations
1	Unveiling the robustness of porphyrin crystalline nanowires toward aggressive chemicals. European Physical Journal Plus, 2022, 137, 1.	2.6	2
2	Nature of Optical Excitations in Porphyrin Crystals: A Joint Experimental and Theoretical Study. Journal of Physical Chemistry Letters, 2021, 12, 869-875.	4.6	4
3	Chemical separation of acrylic color components enabling the identification of the pigment spectroscopic response. European Physical Journal Plus, 2021, 136, 1.	2.6	3
4	Lenticular Ga-oxide nanostructures in thin amorphous germanosilicate layers - Size control and dimensional constraints. Materials and Design, 2021, 204, 109667.	7.0	3
5	Optimization of Copper Stain Removal from Marble through the Formation of Cu(II) Complexes in Agar Gels. Gels, 2021, 7, 111.	4.5	11
6	Detecting the NIR Fingerprint of Colors: The Characteristic Response of Modern Blue Pigments. Heritage, 2019, 2, 2255-2261.	1.9	6
7	Responsive charge transport in wide-band-gap oxide films of nanostructured amorphous alkali-gallium-germanosilicate. Journal of Materials Chemistry C, 2019, 7, 7768-7778.	5.5	2
8	Control of post-growth processes for the selection of metallo-tetraphenylporphyrin nanowires. Physical Chemistry Chemical Physics, 2019, 21, 8482-8488.	2.8	4
9	Reflectance anisotropy spectroscopy applied to organic thin films: The role of the substrate. Organic Electronics, 2018, 62, 102-106.	2.6	4
10	Epitaxy of oligothiophenes on alkali metal hydrogen phthalates: Simulations and experiments. Journal of Chemical Physics, 2017, 146, 124701.	3.0	1
11	Oxidation of Crystalline Rubrene Films: Evidence of an Epitaxial Native Oxide Layer. Advanced Materials Interfaces, 2017, 4, 1700670.	3.7	4
12	Growth and properties of nanostructured titanium dioxide deposited by supersonic plasma jet deposition. Applied Surface Science, 2017, 425, 407-415.	6.1	15
13	Substrate Selection for Full Exploitation of Organic Semiconductor Films: Epitaxial Rubrene on Î²â€Alanine Single Crystals. Advanced Materials Interfaces, 2015, 2, 1500423.	3.7	14
14	Optical and morphological properties of ultra-thin H₂ TPP, H₄ TPP and ZnTPP films. Physica Status Solidi (B): Basic Research, 2015, 252, 100-104.	1.5	7
15	Porphyrin Nanowires with Epitaxially Locked Uniaxial Orientation. Journal of Physical Chemistry C, 2015, 119, 18210-18215.	3.1	11
16	Change of cobalt magnetic anisotropy and spin polarization with alkanethiolates self-assembled monolayers. New Journal of Physics, 2015, 17, 063022.	2.9	15
17	Solid State Organic X-Ray Detectors Based on Rubrene Single Crystals. IEEE Transactions on Nuclear Science, 2015, 62, 1791-1797.	2.0	36
18	Organic Electronics: Stable Alignment of Tautomers at Room Temperature in Porphyrin 2D Layers (Adv.) Tj ETQq0 0 0 rgBT /Overlock 10	14.9	4

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19	Unconventional postâ€deposition chemical treatment on ultraâ€thin H₂TPP film grown on graphite. Crystal Research and Technology, 2014, 49, 581-586.	1.3	9
20	Stable Alignment of Tautomers at Room Temperature in Porphyrin 2D Layers. Advanced Functional Materials, 2014, 24, 958-963.	14.9	51
21	Connecting molecule oxidation to single crystal structural and charge transport properties in rubrene derivatives. Journal of Materials Chemistry C, 2014, 2, 4147-4155.	5.5	25
22	Controlling drop-casting deposition of 2D Pt-octaethyl porphyrin layers on graphite. Synthetic Metals, 2014, 195, 201-207.	3.9	12
23	Probing Two-Dimensional vs Three-Dimensional Molecular Aggregation in Metal-Free Tetraphenylporphyrin Thin Films by Optical Anisotropy. Journal of Physical Chemistry C, 2014, 118, 15649-15655.	3.1	23
24	Photoluminescence and infrared spectroscopy for the study of defects in silicon for photovoltaic applications. Solar Energy Materials and Solar Cells, 2014, 130, 696-703.	6.2	32
25	Patterned Growth of Crystalline Organic Heterostructures. Advanced Materials, 2013, 25, 2804-2808.	21.0	14
26	Epitaxial Interfaces in Rubrene Thin Film Heterostructures. Journal of Physical Chemistry C, 2013, 117, 13981-13988.	3.1	20
27	Epitaxial Growth of Organic Semiconductor Polymorphs on Natural Amino Acid Single Crystals. Crystal Growth and Design, 2013, 13, 4268-4278.	3.0	16
28	Optical Properties of Blends: Influence of Mixing-Induced Disorder in Pentacene:Diindenoperylene versus Perfluoropentacene:Diindenoperylene. Journal of Physical Chemistry C, 2013, 117, 13952-13960.	3.1	15
29	Organic epitaxial layers on organic substrates. Crystal Research and Technology, 2013, 48, 840-848.	1.3	6
30	Growth of pseudomorphic structures through organic epitaxy. Journal of Chemical Physics, 2012, 137, 224703.	3.0	6
31	Experimental assessment of nonergodicity in tetracene single crystals. Physical Review B, 2012, 86, .	3.2	12
32	Grazing-incidence X-ray diffraction study of rubrene epitaxial thin films. Journal of Synchrotron Radiation, 2012, 19, 682-687.	2.4	14
33	Stability to photo-oxidation of rubrene and fluorine-substituted rubrene. Synthetic Metals, 2012, 161, 2603-2606.	3.9	26
34	Dye-sensitized solar cells: spectroscopic evaluation of dye loading on TiO2. Journal of Materials Chemistry, 2012, 22, 11364.	6.7	73
35	Unique Orientation of Organic Epitaxial Thin Films: The Role of Intermolecular Interactions at the Interface and Surface Symmetry. Journal of Physical Chemistry C, 2011, 115, 5880-5885.	3.1	25
36	Control of Ï€âˆ’Ï€ Interactions in Epitaxial Films of Platinum(II) Octaethyl Porphyrin. Chemistry of Materials, 2011, 23, 832-840.	6.7	24

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37	Oxidation Dynamics of Epitaxial Rubrene Ultrathin Films. Chemistry of Materials, 2011, 23, 3246-3253.	6.7	26
38	Organicâ€organic heteroepitaxy: facts, concepts and perspectives. Crystal Research and Technology, 2011, 46, 827-832.	1.3	15
39	Probing phase transitions and stability of organic semiconductor single crystals by dielectric investigation. Journal of Applied Physics, 2011, 109, 013529.	2.5	16
40	Magnetic behaviour of polyfluoroacridine-based organic molecular materials. European Physical Journal B, 2010, 73, 495-501.	1.5	2
41	Novel organic paramagnetic nanofibers and nanostructures: A spectroscopic investigation. Chemical Physics Letters, 2010, 498, 129-133.	2.6	0
42	Reflectance anisotropy spectroscopy: A probe to explore organic epitaxial growth. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 1029-1034.	2.1	16
43	Pseudomorphic growth of organic semiconductor thin films driven by incommensurate epitaxy. Applied Physics Letters, 2009, 94, 073307.	3.3	17
44	Kinetic Phase Selection of Rubrene Heteroepitaxial Domains. Journal of Physical Chemistry C, 2009, 113, 20927-20933.	3.1	33
45	Kelvin Probe Force Microscopy Characterization of Self-Assembled Monolayers on Metals Deposited with Dip-Pen Nanolithography. Journal of Physical Chemistry C, 2009, 113, 8329-8335.	3.1	10
46	Effect of functionalization on the self-assembling propensity of Î²-sheet forming peptides. Soft Matter, 2009, 5, 660-668.	2.7	41
47	Organicâ"Organic Heteroepitaxy of Semiconductor Crystals: Î±-Quaterthiophene on Rubrene. Chemistry of Materials, 2009, 21, 4859-4867.	6.7	36
48	Epitaxially grown sexiphenyl nanocrystals on the organic KAP(010) surface. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 41, 133-137.	2.7	30
49	In-situ study of the interface formation in organic multilayers. Superlattices and Microstructures, 2008, 44, 550-555.	3.1	1
50	Bulk electrical properties of rubrene single crystals: Measurements and analysis. Physical Review B, 2008, 77, .	3.2	43
51	Growth-related properties and postgrowth phenomena in organic molecular thin films. Journal of Chemical Physics, 2007, 127, 244703.	3.0	10
52	Using atomic force microscopy to reveal the nature of extended defects in organic semiconductors: the role of crystal growth mechanisms. Journal of Physics: Conference Series, 2007, 61, 831-835.	0.4	6
53	Measurement of carrier transport and injection in metal-free tetraphenylporphyrin. Synthetic Metals, 2007, 157, 1029-1033.	3.9	1
54	Homoepitaxial Growth of Î±-Hexathiophene. Journal of Physical Chemistry C, 2007, 111, 12741-12746.	3.1	24

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55	Heteroepitaxy of Î±-Quaterthiophene on Tetracene Single Crystals. Journal of Physical Chemistry C, 2007, 111, 19009-19014.	3.1	22
56	Epitaxial growth of organic heterostructures: Morphology, structure, and growth mode. Surface Science, 2007, 601, 2571-2575.	1.9	18
57	Real time detection of the epitaxial growth of oligothiophene layers by reflectance anisotropy spectroscopy. Surface Science, 2007, 601, 4488-4491.	1.9	7
58	Comment on: â€œMagnetic field influence on the molecular alignment of vanadyl phthalocyanine thin filmsâ€•by. Journal of Crystal Growth, 2007, 299, 436.	1.5	0
59	Extended defects in organic molecular semiconductors: the role of crystal growth mechanisms. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 711-714.	0.8	3
60	Formation of Ge islands from a Ge layer on Si substrate during post-growth annealing. Applied Surface Science, 2007, 253, 3034-3040.	6.1	6
61	Incommensurate Epitaxy of Tetrathiophene on Potassium Hydrogen Phthalate:â€‰ Insights from Molecular Simulation. Crystal Growth and Design, 2006, 6, 1826-1832.	3.0	34
62	Direct observation of the epitaxial growth of molecular layers on molecular single crystals. Applied Physics Letters, 2006, 89, 261905.	3.3	19
63	Organicâ^'Organic Epitaxy of Incommensurate Systems:Â Quaterthiophene on Potassium Hydrogen Phthalate Single Crystals. Journal of the American Chemical Society, 2006, 128, 13378-13387.	13.7	71
64	Strategies for two-dimensional growth of organic molecular films. Chemical Physics, 2006, 325, 193-206.	1.9	33
65	XRR and GISAXS study of silicon oxynitride films. Applied Surface Science, 2006, 253, 33-37.	6.1	4
66	Absorbance spectra of polycrystalline samples and twinned crystals of oligothiophenes. Applied Surface Science, 2006, 253, 271-274.	6.1	12
67	Structural characterisation of ultra-high vacuum sublimated polycrystalline thin films of hexathiophene. Thin Solid Films, 2006, 500, 169-173.	1.8	8
68	Growth and characterisation of all-organic heterostructures. , 2006, 6192, 427.		0
69	Tetracene thin films grown by organic molecular beam deposition under a static magnetic field. Journal of Chemical Physics, 2006, 124, 224705.	3.0	7
70	Coherent excitonic emission in molecular semiconductors. Journal of Luminescence, 2005, 112, 402-406.	3.1	0
71	Directional dispersion in quaterthiophene single crystals and oriented thin films. Journal of Luminescence, 2005, 112, 312-315.	3.1	7
72	Trap state photoluminescence in solid state quaterthiophene. Thin Solid Films, 2005, 474, 230-234.	1.8	4

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73	Tuning the growth mode in organic molecular-beam epitaxy. Physical Review B, 2005, 71, .	3.2	23
74	Magnetically Driven Growth of Anthracene Thin Films by Organic Molecular Beam Deposition. Journal of Physical Chemistry B, 2005, 109, 5150-5155.	2.6	9
75	Structural characterisation of single crystals and thin films of Î±,Ï‰-dihexylquaterthiophene. Journal of Materials Chemistry, 2005, 15, 2444.	6.7	33
76	Role of Desorption in the Growth Process of Molecular Organic Thin Films. Journal of Physical Chemistry B, 2005, 109, 7859-7864.	2.6	19
77	In situoptical investigation of oligothiophene layers grown by organic molecular beam epitaxy. Journal of Physics Condensed Matter, 2004, 16, S4393-S4402.	1.8	12
78	Evidence of postdeposition nucleation in organic molecular thin films. Physical Review B, 2004, 69, .	3.2	11
79	Thickness measurements by quartz microbalance during thin-film growth by organic-molecular-beam deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 482.	2.1	23
80	Anisotropic optical functions of pentaerythrytol, an uniaxial organic crystal. Thin Solid Films, 2004, 455-456, 576-580.	1.8	5
81	Structural and optical study on a single crystal of a novel fluorinated acridine. European Physical Journal B, 2004, 39, 229-234.	1.5	3
82	The application of reflectance anisotropy spectroscopy to organics deposition. Organic Electronics, 2004, 5, 73-81.	2.6	40
83	Structural characterisation of polycrystalline $alpha;,$omega;-dihexyl quaterthiophene thin films by transmission electron microscopy. Organic Electronics, 2004, 5, 141-145.	2.6	4
84	Organisation, structure and morphology of organic thin films via electron microscopy. Organic Electronics, 2004, 5, 7-22.	2.6	5
85	Absorption and propagation of light in quaterthiophene crystals. Journal of Luminescence, 2004, 110, 212-216.	3.1	1
86	Preparation of highly pure quaterthiophene and role of impurities on its photoluminescence properties. Journal of Materials Chemistry, 2004, 14, 171-178.	6.7	42
87	Small angle X-ray scattering study of oxygen precipitation in silicon. Nuclear Instruments & Methods in Physics Research B, 2003, 200, 105-109.	1.4	0
88	Gap states produced by oxygen precipitation in Czochralski silicon. Vacuum, 2003, 71, 141-145.	3.5	2
89	Absorption coefficient of oxide precipitates in silicon wafers after different three-step annealing. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 247-250.	3.5	1
90	Regioregular polythiophene field-effect transistors employed as chemical sensors. Sensors and Actuators B: Chemical, 2003, 93, 257-262.	7.8	77

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91	Superradiance in Molecular H Aggregates. Physical Review Letters, 2003, 91, 247401.	7.8	117
92	Characterization of organic semiconductors by a large-signal capacitanceâ€“voltage method at high and low frequencies. Synthetic Metals, 2003, 138, 15-19.	3.9	12
93	Charge injection and transport in tetra-phenyl-porphyrin. Synthetic Metals, 2003, 138, 255-260.	3.9	4
94	Absorption and emission properties of Î±,Ï‰-dihexyl-quaterthiophene thin films grown by organic molecular beam deposition. Synthetic Metals, 2003, 138, 55-58.	3.9	6
95	Reflectance spectra of quinquethiophene single crystals. Synthetic Metals, 2003, 139, 873-875.	3.9	6
96	Transmittance and reflectance spectra of crystalline Î±,Ï‰-dihexyl-quaterthiophene thin films. Synthetic Metals, 2003, 139, 877-880.	3.9	2
97	Coherent emission from crystalline oligothiophenes with an even number of rings. Synthetic Metals, 2003, 139, 765-768.	3.9	0
98	Crystal structure of polycrystalline films of quaterthiophene grown by organic molecular beam deposition. Synthetic Metals, 2003, 138, 125-130.	3.9	29
99	Synthesis and Properties of Some Derivatives of 1,2,3,4-Tetrafluoroacridine for Solid State Emitting Systems. Chemistry of Materials, 2003, 15, 5010-5018.	6.7	23
100	Growth dynamics of quaterthiophene thin films. Journal of Materials Chemistry, 2003, 13, 1669.	6.7	20
101	Highly sensitive optical monitoring of molecular film growth by organic molecular beam deposition. Applied Physics Letters, 2003, 83, 4146-4148.	3.3	37
102	Broad and narrow bands in the photoluminescence spectrum of solid-state oligothiophenes: Two marks of an intrinsic emission. Physical Review B, 2003, 67, .	3.2	22
103	Intrinsic Excitonic Luminescence in Odd and Even Numbered Oligothiophenes. Physical Review Letters, 2002, 89, 157403.	7.8	51
104	Studies of photoreflectance spectra in Cd1â^'xMnxTe/CdTe superlattices with high compositions. Journal of Applied Physics, 2002, 92, 5169-5172.	2.5	4
105	Influence of molecular arrangement and morphology on optical spectra of oligothiophene heterostructures grown by organic molecular-beam deposition. Physical Review B, 2002, 65, .	3.2	12
106	Influence of oxygen precipitation on the measure of interstitial oxygen concentration in silicon from the 1207 cmâ^'1 infrared absorption band. Journal of Applied Physics, 2002, 91, 166.	2.5	2
107	Temperature activated de-trapping processes in vacuum deposited sexithiophene thin films. Synthetic Metals, 2002, 128, 63-66.	3.9	9
108	Influence of the substrate on the growth of Î±,Ï‰-dihexyl-quaterthiophene thin films by organic molecular beam deposition. Journal of Crystal Growth, 2002, 235, 241-247.	1.5	6

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109	Stray-light induced artefacts in absorption spectra of crystalline oligothiophenes. European Physical Journal B, 2002, 28, 385-388.	1.5	30
110	Defects Involving Oxygen in Crystalline Silicon. Solid State Phenomena, 2001, 85-86, 285-316.	0.3	4
111	Optical properties of thin films of oligothiophenes deposited by organic molecular beam deposition. Synthetic Metals, 2001, 116, 213-216.	3.9	6
112	The origin of radiative emission of quaterthiophene ultra-thin films. Synthetic Metals, 2001, 121, 1355-1356.	3.9	14
113	Absorption coefficient of sexithiophene thin films grown by organic molecular beam deposition. Synthetic Metals, 2001, 121, 1419-1420.	3.9	4
114	Growth of quaterthiophene thin films on potassium acid phthalate by organic molecular beam deposition. Synthetic Metals, 2001, 121, 1421-1422.	3.9	9
115	Electrical characterization of organic semiconductors by transient current methods. Synthetic Metals, 2001, 122, 169-171.	3.9	7
116	Optical properties of oligothiophene hetero-structures grown by organic molecular beam deposition. Synthetic Metals, 2001, 124, 71-73.	3.9	0
117	Epitaxial growth of quaterthiophene thin films by organic molecular beam deposition. Vacuum, 2001, 61, 193-197.	3.5	9
118	Crystal Structure of Epitaxial Quaterthiophene Thin Films Grown on Potassium Acid Phthalate. Advanced Materials, 2001, 13, 127-130.	21.0	45
119	Generalized anisotropic ellipsometry applied to an organic single crystal: Potassium acid phthalate. Journal of Applied Physics, 2001, 90, 3838-3842.	2.5	16
120	Measurement of interstitial oxygen concentration in silicon below 1015â€Šatoms/cm3. Applied Physics Letters, 2001, 79, 4339-4341.	3.3	7
121	Evaluation of the precipitate contribution to the infrared absorption in interstitial oxygen measurements in silicon. Applied Physics Letters, 2001, 79, 4106-4108.	3.3	3
122	Thermal model of Knudsen cells for organic molecular beam deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 878-882.	2.1	6
123	Infrared characterization of oxygen precipitates in silicon wafers with different concentrations of interstitial oxygen. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 73, 145-148.	3.5	14
124	Influence of different growth and nucleation times on optical spectra of precipitated oxygen in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 73, 149-153.	3.5	7
125	Optical absorption of precipitated oxygen in silicon at liquid helium temperature. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 73, 224-229.	3.5	9
126	Optical properties of highly oriented quaterthiophene thin films grown by organic molecular-beam deposition. Physical Review B, 2000, 62, 11170-11176.	3.2	30

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127	Quasi-epitaxial growth of quaterthiophene thin films by organic molecular beam deposition. Synthetic Metals, 2000, 115, 69-73.	3.9	1
128	Growth of ordered thin films of tris(phenylquinoxaline) by organic molecular beam deposition. Synthetic Metals, 2000, 111-112, 99-103.	3.9	0
129	Photoexcitations in oriented tetrahexyl-sexithiophene thin films. Physical Review B, 1999, 60, 6039-6044.	3.2	12
130	Structural characterization of tetrahexyl sexithiophene ordered films grown by organic molecular beam deposition. Optical Materials, 1999, 12, 301-305.	3.6	9
131	Molecular beam deposition of thin films of organic semiconductors. Journal of Crystal Growth, 1999, 201-202, 1044-1048.	1.5	6
132	Raman line profile in polycrystalline silicon. Journal of Applied Physics, 1999, 86, 4383-4386.	2.5	19
133	Optical properties of oriented thin films of oligothiophenes. Synthetic Metals, 1999, 101, 538-541.	3.9	15
134	Growth of ultrathin films of substituted sexithiophene by organic molecular beam deposition. Synthetic Metals, 1999, 101, 530-531.	3.9	1
135	Infrared response of oxygen precipitates in silicon: Experimental and simulated spectra. Applied Physics Letters, 1999, 75, 1131-1133.	3.3	33
136	Excited State Electronic Interactions in Oligothiophenes with Novel Supramolecular Structure. Materials Research Society Symposia Proceedings, 1999, 598, 278.	0.1	0
137	Influence of roughness and grain dimension on the optical functions of polycrystalline silicon films. Thin Solid Films, 1998, 313-314, 243-247.	1.8	7
138	Spectroscopic ellipsometry measurements on an anisotropic organic crystal: potassium acid phtalate. Thin Solid Films, 1998, 313-314, 347-350.	1.8	7
139	Organic Molecular Beam Deposition of Highly Oriented Î²â€Tetrahexylsexithiophene Films. Advanced Materials, 1998, 10, 931-934.	21.0	35
140	Annealing effects on silicon-rich oxide films studied by spectroscopic ellipsometry. Thin Solid Films, 1998, 325, 36-41.	1.8	12
141	A new apparatus for ultra-high vacuum organic molecular beam deposition. Optical Materials, 1998, 9, 437-444.	3.6	40
142	Orientation and order of Î²-tetrahexyl-sexithiophene molecules deposited by organic molecular beam deposition. Synthetic Metals, 1998, 98, 83-86.	3.9	8
143	Quantitative Evaluation of Precipitated Oxygen in Silicon by Infrared Spectroscopy: Still an Open Problem. Journal of the Electrochemical Society, 1998, 145, 1715-1719.	2.9	9
144	Ellipsometric characterization of amorphous and polycrystalline silicon films deposited using a single wafer reactor. Applied Physics Letters, 1997, 70, 892-894.	3.3	16

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145	Infrared study of Si-rich silicon oxide films deposited by plasma-enhanced chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 377-389.	2.1	86
146	Optical properties of polycrystalline silicon thin films deposited by single-wafer chemical vapor deposition. Thin Solid Films, 1997, 296, 91-93.	1.8	5
147	Infrared Study of Oxygen Segregation at Structural Defects in Polycrystalline Silicon. , 1997, , 485-487.		2
148	Cross-sectional Infrared Transmission Measurements for Highly Sensitive Thin Film Characterization. , 1997, , 343-344.		0
149	Optical characterization of amorphous dielectric films. Advanced Materials, 1996, 8, 349-352.	21.0	4
150	Siî—¸H bonding configuration in SiOx: N,H films deposited by chemical vapor deposition. Solid State Communications, 1996, 100, 657-661.	1.9	16
151	Non-doping light impurities in silicon for solar cells. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 36, 55-62.	3.5	9
152	Surface mode excitation in platelet SiOx precipitates in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 36, 221-224.	3.5	0
153	Optical response of Cu3Ge thin films. Journal of Applied Physics, 1996, 79, 8115-8117.	2.5	10
154	Non-doping light impurities in silicon for solar cells. , 1996, , 55-62.		0
155	Surface mode excitation in platelet SiOx precipitates in silicon. , 1996, , 221-224.		0
156	Highly Sensitive Optical Method for the Characterization of $f SiO_{2}$ Films in Bonded Wafers. Japanese Journal of Applied Physics, 1995, 34, L1409-L1411.	1.5	4
157	Oxygen precipitation in silicon. Journal of Applied Physics, 1995, 77, 4169-4244.	2.5	466
158	Silicon oxynitride study by the tetrahedron model and by spectroscopic ellipsometry. Journal of Non-Crystalline Solids, 1995, 187, 395-402.	3.1	10
159	Spectroscopic study of SiCâ€like structures formed on polycrystalline silicon sheets during growth. Journal of Applied Physics, 1994, 75, 3586-3592.	2.5	19
160	Experimental evidence of the crossover between bulk and thin-film optics. Physical Review B, 1994, 50, 17756-17758.	3.2	9
161	Induction-model analysis of Siî—¸H stretching mode in porous silicon. Solid State Communications, 1994, 89, 615-618.	1.9	37
162	Giant Faraday rotation in diluted magnetic semiconductor Cd1â^'Ï‡FeÏ‡TeÏ‡. Solid State Communications, 1994, 92, 725-729.	1.9	7

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163	Stoichiometry of oxygen precipitates in silicon. Applied Surface Science, 1993, 63, 245-248.	6.1	13
164	Ellipsometric characterization of hydrogen-rich oxynitride films. Thin Solid Films, 1993, 233, 227-230.	1.8	4
165	Characterization of porous silicon inhomogeneities by high spatial resolution infrared spectroscopy. Solid State Communications, 1993, 87, 1-4.	1.9	78
166	Oxygen precipitates in short-time annealed Czochralski silicon. Journal of Crystal Growth, 1993, 126, 63-69.	1.5	7
167	Homogeneity of carbon microdistribution in edge-defined film-fed grown polycrystalline silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 18, 122-128.	3.5	6
168	Optical characterization of oxynitride films in the visible-ultraviolet range. Applied Physics A: Materials Science and Processing, 1993, 56, 147-152.	2.3	13
169	Spectroscopic ellipsometry study of the relaxation state of amorphous silicon. Thin Solid Films, 1993, 233, 203-206.	1.8	9
170	Magnetization and magnetic susceptibility of the diluted magnetic semiconductor Cd1â^'xMnxGa2Se4. Journal of Applied Physics, 1993, 73, 5736-5738.	2.5	2
171	Tetrahedron model for the optical dielectric function of H-rich silicon oxynitride. Physical Review B, 1993, 48, 14208-14215.	3.2	22
172	Characterization of silicon dioxide and phosphosilicate glass deposited films. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 2081.	1.6	32
173	InsituCr gettering in polycrystalline silicon sheets obtained by edgeâ€defined filmâ€fed growth. Applied Physics Letters, 1993, 62, 2664-2666.	3.3	13
174	Stoichiometry of oxygen precipitates in silicon. , 1993, , 245-248.		0
175	Oxygen Behavior during Silicon Epitaxial Growth: Recent Advances. Materials Science Forum, 1992, 83-87, 1069-1074.	0.3	2
176	Infrared determination of interstitial oxygen behavior during epitaxial silicon growth on Czochralski substrates. Journal of Applied Physics, 1992, 72, 4313-4320.	2.5	4
177	Polarization effect on infrared absorption of oxygen precipitates in silicon. Applied Physics Letters, 1992, 60, 871-873.	3.3	14
178	Effect of annealing on carbon concentration in edgeâ€defined filmâ€fed grown polycrystalline silicon. Journal of Applied Physics, 1992, 71, 3785-3787.	2.5	11
179	Infrared study of oxygen precipitate composition in silicon. Physical Review B, 1992, 46, 4123-4127.	3.2	40
180	Boron accumulation at epi-substrate silicon interface during epitaxial growth. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1992, 15, 32-36.	3.5	0

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181	Optical absorption edge of Cd1âˆ’x Mn x Ga2Se4 crystals. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1992, 14, 33-39.	0.4	3
182	Quantitative determination of highâ€temperature oxygen microprecipitates in Czochralski silicon by microâ€Fourier transform infrared spectroscopy. Applied Physics Letters, 1991, 58, 2099-2101.	3.3	16
183	Interaction of ambient gas and meniscus surface during growth of edgeâ€defined filmâ€fed growth polycrystalline silicon samples. Journal of Applied Physics, 1991, 70, 2963-2967.	2.5	11